TOSHIBA GTR Module Silicon N Channel IGBT

# MG200J2YS50

## High Power Switching Applications Motor Control Applications

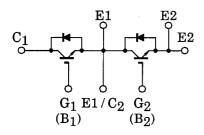
- The electrodes are isolated from case.
- High input impedance
- Includes a complete half bridge in one package.
- Enhancement-mode
- High Speed :  $t_f = 0.30 \mu s \text{ (Max) (IC} = 200 \text{A)}$

 $t_{rr} = 0.15 \mu s \text{ (Max) (IF} = 200 \text{A)}$ 

• Low saturation voltage

:  $V_{CE (sat)} = 2.70 V (Max) (I_{C} = 200 A)$ 

## **Equivalent Circuit**



# Unit: mm 2-\$5.4±0.3 3-M5 4-FAST-ON-TAB #110 4-FAST-ON-TAB

## Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	600	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	Ic	200	Α	
	1ms	I <sub>CP</sub>	400		
Forward current	DC	I <sub>F</sub>	200	Α	
	1ms	I <sub>FM</sub>	400		
Collector power dissipation (Tc = 25°C)		PC	900	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

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damage to property.

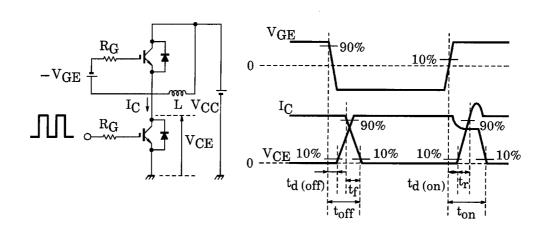
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## **Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I <sub>GES</sub>	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0	_	_	±500	nA	
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0	_	_	2.0	mA	
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 5V	5.0	7.0	8.0	V	
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 200A, V <sub>GE</sub> = 15V	_	2.10	2.70	V	
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz	_	18000	_	pF	
Switching time	Turn-on delay time	t <sub>d (on)</sub>	Inductive load $V_{CC} = 300V$ $I_{C} = 200A$ $V_{GE} = \pm 15V$ $R_{G} = 4.2\Omega$ (Note 1)	_	0.15	0.30	- μs	
	Rise time	t <sub>r</sub>		_	0.15	0.30		
	Turn-on time	t <sub>on</sub>		_	0.50	1.00		
	Turn-off delay time	t <sub>d (off)</sub>		_	0.20	0.40		
	Fall time	t <sub>f</sub>		_	0.15	0.30		
	Turn-off time	t <sub>off</sub>		_	0.50	1.00		
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 200A, V <sub>GE</sub> = 0	_	2.30	3.00	V	
Reverse recovery time		t <sub>rr</sub>	I <sub>F</sub> = 200A, V <sub>GE</sub> = -10V di / dt = 200A / μs	_	0.08	0.15	μs	
Thermal resistance		R <sub>th (j-c)</sub>	Transistor stage	_	_	0.14	°C/W	
			Diode stage	_	_	0.35	C/W	

Note 1: Switching time test circuit & timing chart

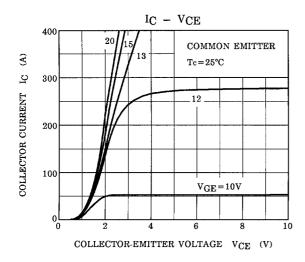


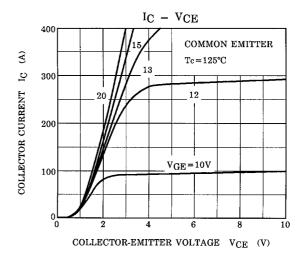
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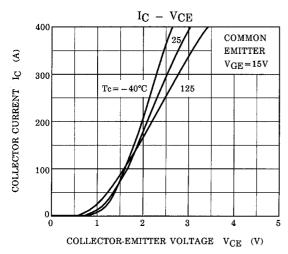
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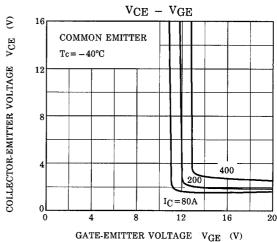
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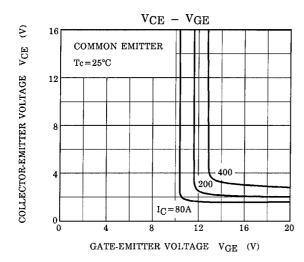
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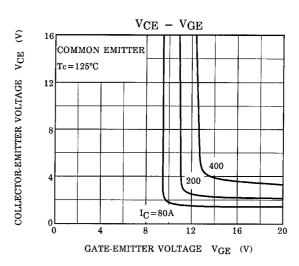


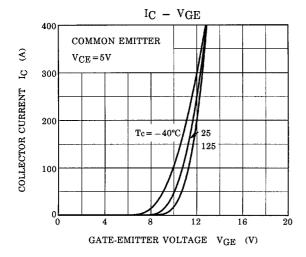


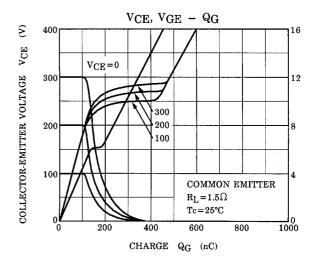


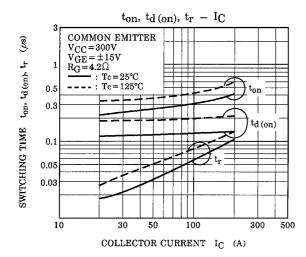


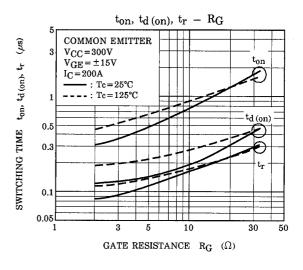


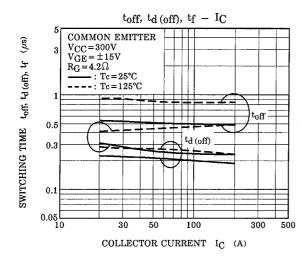


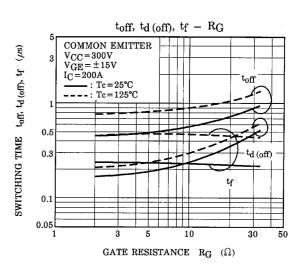


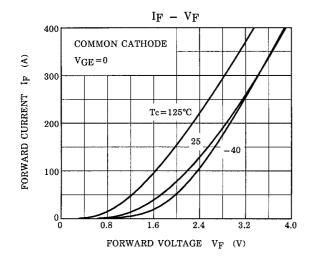


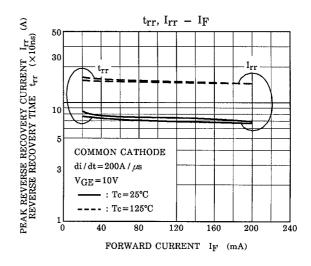


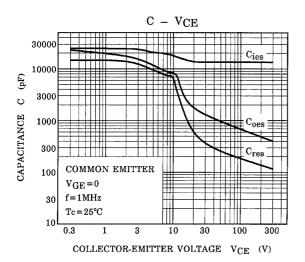


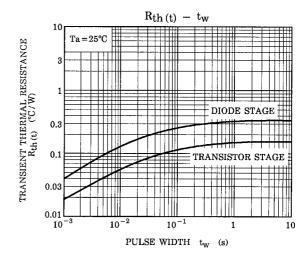


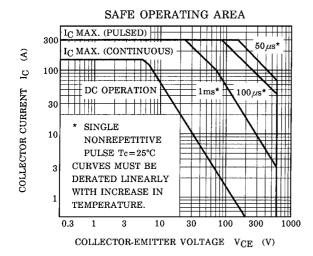


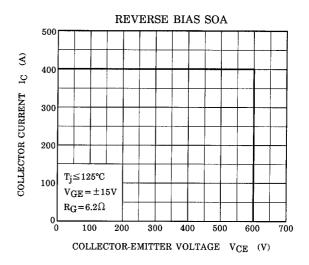












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